

CLAIMS AMENDMENTS:

1. (Third Times Amended) An integrated circuit comprising:
 - a dielectric layer formed over a substrate;
 - a damascene structure in the dielectric layer, the damascene structure comprising a bottom surface and first and second sidewalls;
 - a conductor located in the damascene structure, the conductor comprising a conductive material; and
 - a liner layer lining the bottom surface and sidewalls of the damascene structure and [contacts first, second, and third surfaces] encapsulating the conductor by contacting a top surface of the conductor, the liner layer imparts a random grain orientation in the conductive material of the conductor to improve electromigration lifetime of the conductor.
2. (Twice Amended) An integrated circuit of claim 1, wherein [the] a conductive material of the liner comprises a random grain orientation.
3. (Twice Amended) An integrated circuit of claim 1, wherein [the] a conductive material of the liner comprises an amorphous character.
4. (Twice Amended) An integrated circuit of claim 1, wherein [the] a conductive material of the liner is chosen from a group consisting essentially of titanium nitride, tantalum and tantalum nitride.

5. (Twice Amended) An integrated circuit of claim 1, wherein [the] a conductive material of the liner comprises a random grain orientation or amorphous character.